

ABSTRACT OF THE DISCLOSURE

A method of forming a more satisfactory inorganic compound solid (ferroelectric film or the like) out of organic compound materials containing metal elements by annealing at a relatively low temperature. In order to form a ferroelectric film, a solution of organic compound materials containing metal elements is coated over a semiconductor substrate (S41) and dried (S42), after which precalcining is carried out (S43). After this process is repeated until a predetermined film thickness is achieved, organic substance removing treatment is carried out (S45). The organic substance removing treatment is carried out by, for example, heat treatment (approximately at 550°C) in a low-pressure atmosphere (approximately at 50 Torr). Post calcining is carried out to inorganic compound materials obtained by the organic substance removing treatment (S46). The post calcining is carried out at a temperature of approximately 550°C, for example, whereby the inorganic compound materials are crystallized.

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